Lead-free Green

100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)\ max}$	I_D T_A = +25°C
100V	220mΩ @ V_{GS} = 10V	1.6A
	250mΩ @ V_{GS} = 4.5V	1.3A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

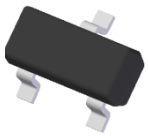
Applications

- Load Switch

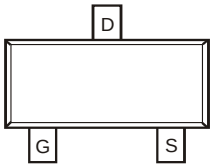
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed Over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.0072 grams (Approximate)

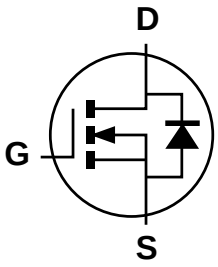
SOT23



Top View



Pin Configuration



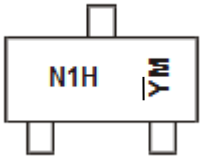
Equivalent Circuit

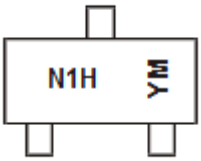
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN10H220L-7	Standard	SOT23	3000/Tape & Reel
DMN10H220L-13	Standard	SOT23	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





N1H = Marking Code
YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
$\overline{Y}$M = Date Code Marking for CAT (Chengdu Assembly/ Test site)
Y or $\overline{Y}$ = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2013	2014	2015	2016	2017	2018	2019
Code	A	B	C	D	E	F	G

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	±16	V
Continuous Drain Current (Note 5) V_{GS} = 10V	(Note 6)	T_A = +25°C T_A = +70°C	I_D	1.6 1.3	A
	(Note 5)	T_A = +25°C T_A = +70°C	I_D	1.4 1.1	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.6	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.3	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\Theta JA}$	94	°C/W
	(Note 5)		177	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 100V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1	—	2.5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	—	220	mΩ	V_{GS} = 10V, I_D = 1.6A
			—	250		V_{GS} = 4.5V, I_D = 1.3A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 1.1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	401	—	pF	V_{DS} = 25V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	22	—		
Reverse Transfer Capacitance	C_{rss}	—	17	—		
Gate Resistance	R_g	—	2.1	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	4.1	—	nC	V_{DS} = 50V, I_D = 1.6A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	8.3	—		
Gate-Source Charge	Q_{gs}	—	1.5	—		
Gate-Drain Charge	Q_{gd}	—	2	—		
Turn-On Delay Time	$t_{D(on)}$	—	6.8	—	ns	V_{DS} = 50V, V_{GS} = 4.5V, R_G = 6.8Ω, I_D = 1A
Turn-On Rise Time	t_r	—	8.2	—		
Turn-Off Delay Time	$t_{D(off)}$	—	7.9	—		
Turn-Off Fall Time	t_f	—	3.6	—		
Reverse Recovery Time	t_{rr}	—	17	—	ns	I_F = 1.1A, di/dt =100A/µs
Reverse Recovery Charge	Q_{rr}	—	9.8	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
7 .Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

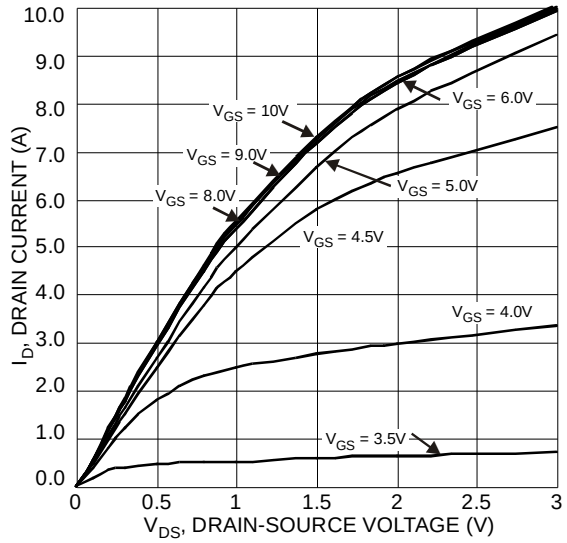


Figure 1 Typical Output Characteristic

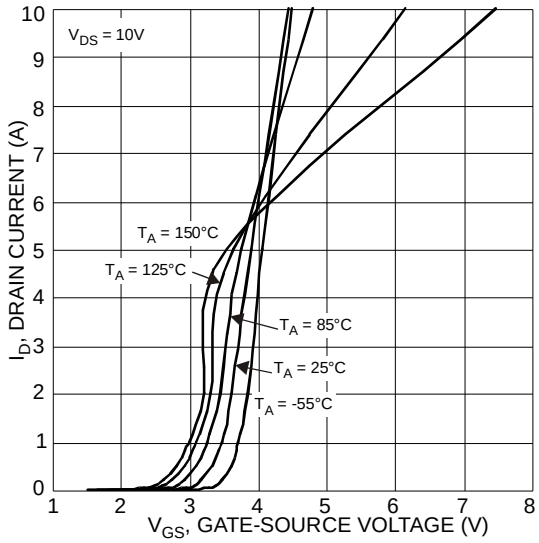


Figure 2 Typical Transfer Characteristics

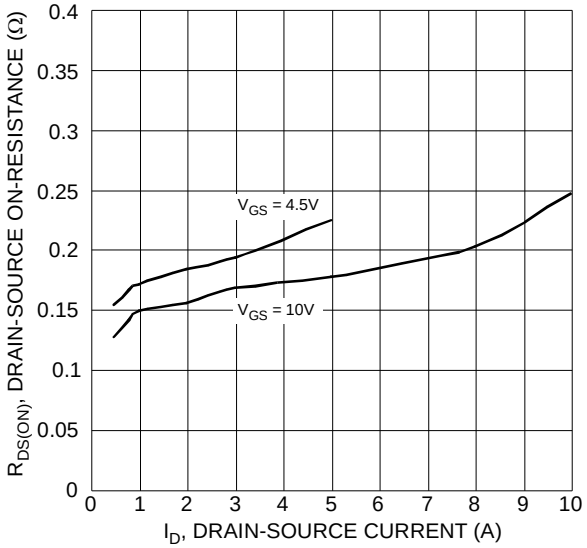


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

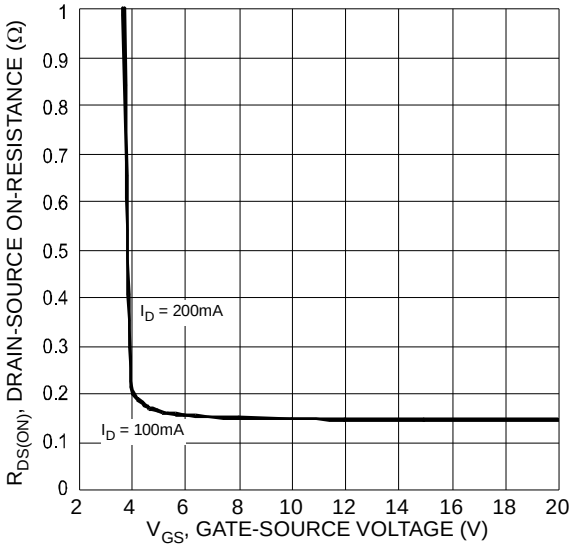


Figure 4 Typical Transfer Characteristic

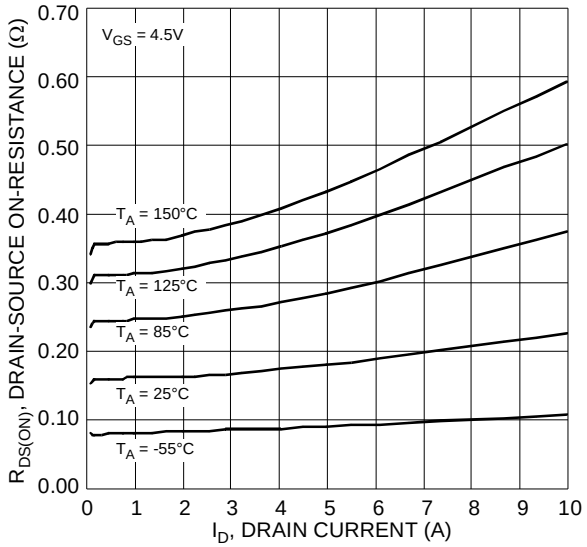


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

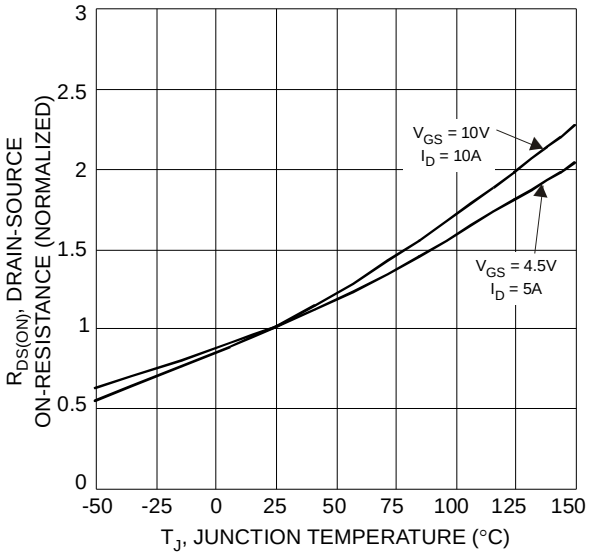


Figure 6 On-Resistance Variation with Temperature

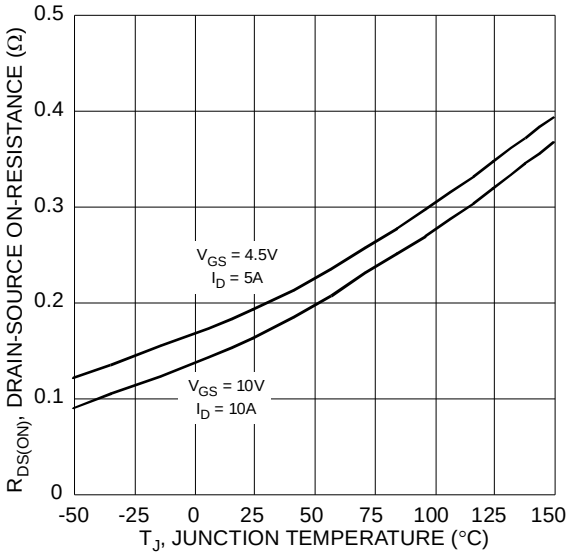


Figure 7 On-Resistance Variation with Temperature

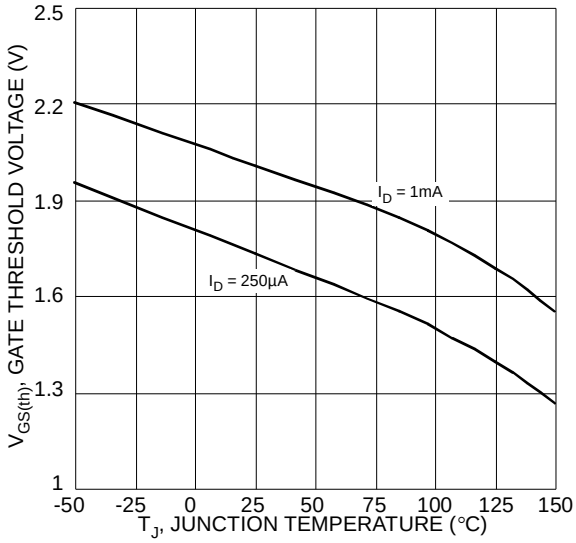


Figure 8 Gate Threshold Variation vs. Ambient Temperature

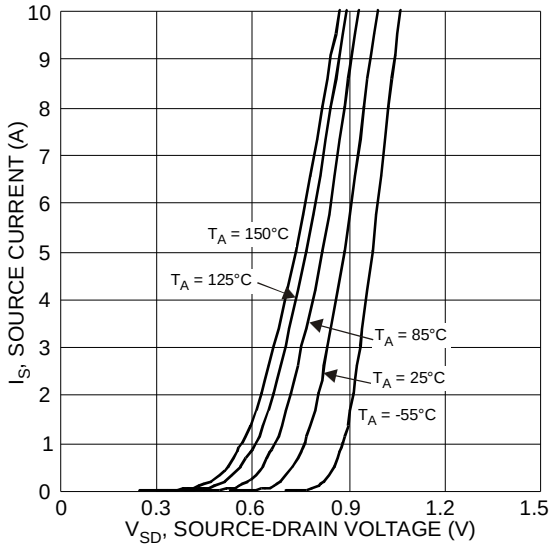


Figure 9 Diode Forward Voltage vs. Current

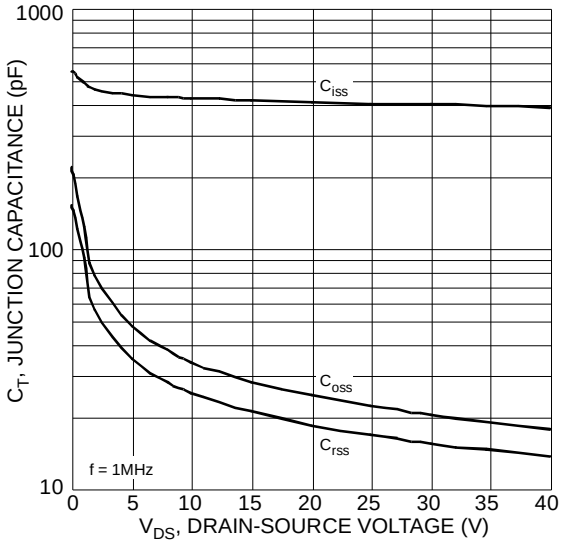


Figure 10 Typical Junction Capacitance

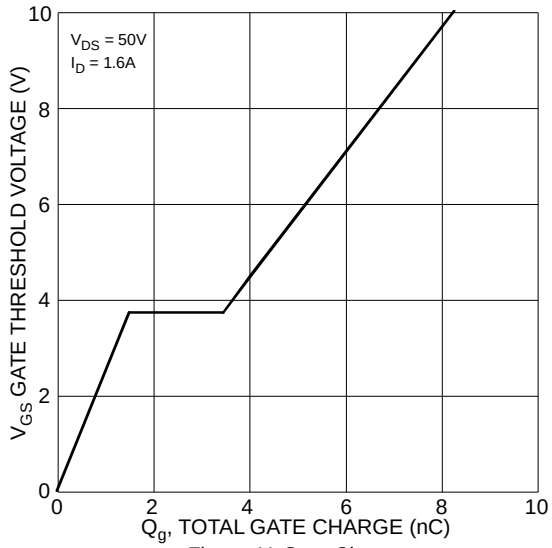


Figure 11 Gate Charge

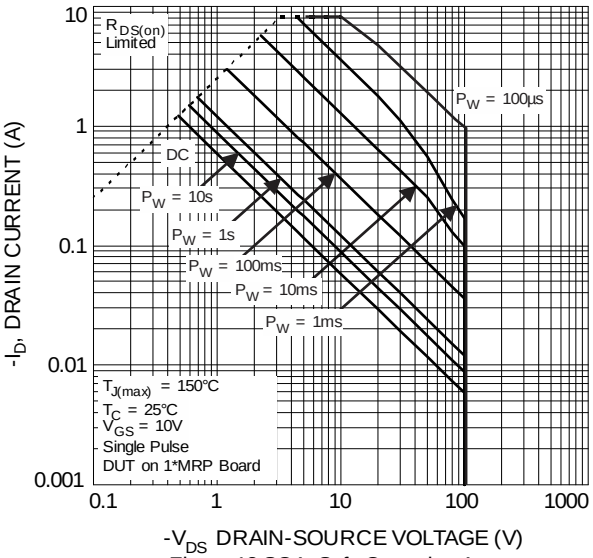


Figure 12 SOA, Safe Operation Area

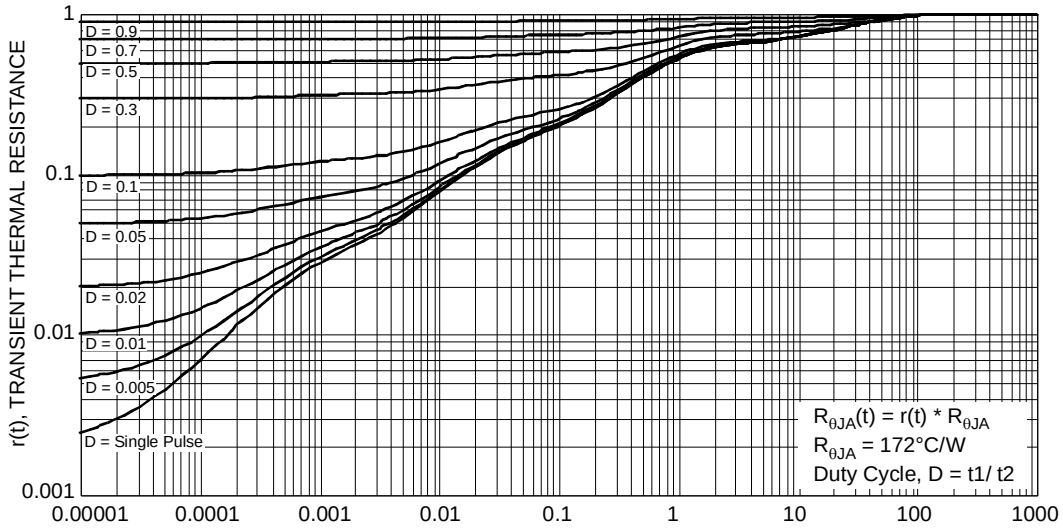
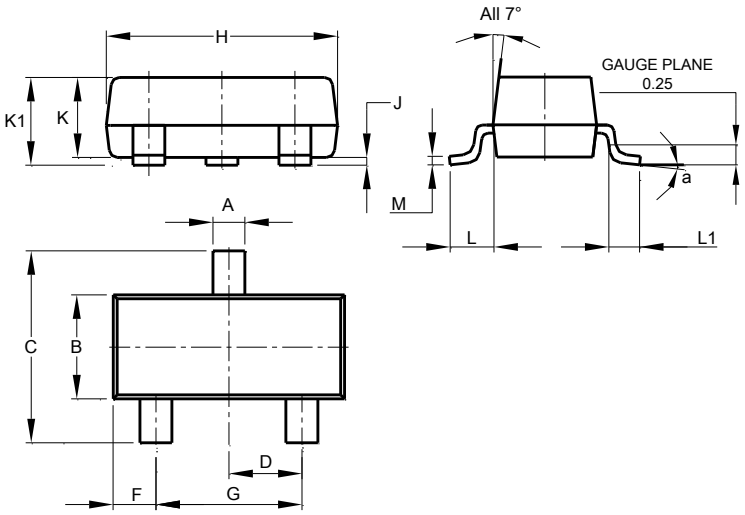


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

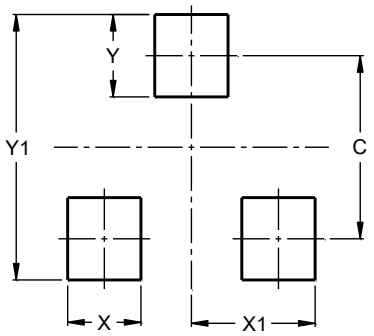


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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